

ProMOS Technologies 0.12um 256Mb DDR DRAM Passes IBM and Dell Product Qualification

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ProMOS Technologies, one of the global leading memory makers, today (August 19) announced that its self-developed 0.12-micron 256Mb DDR [DRAM](#) passed [IBM](#) and Dell OEM customers' stringent product qualification, demonstrating advanced technology developing caliber recognized by its first-tier partners as well.

Aside from this 0.12-micron technology node exclusively developed by ProMOS R&D caliber, Dr. Lin, spokesman and senior business director, pinpointed the core features that the gross die increased 30% if compared with 0.14-micron and reached cross over, consequently saved around 30% cost, which is fairly competitive to industry leading peers' 0.11 micron technology. ProMOS used 248nm scanner to save equipment purchase and prolong 200mm fab utilization. 0.12-micron process technology is expected to account for around 30% of technology allocation in Q3, further ramp up to around 60% in Q4.

ProMOS current monthly output amounts to 2500 chips (256Mb equipment), 256Mb DDR DRAM accounting for around 80% of monthly outputs. The 256Mb DDR DRAM had sold in contract and module markets since this May, the passing of qualification can further enhance ProMOS second half of this year operation performance. Current monthly wafer start at 300mm fab reaches 18,000 wafers and had manufacturing process improvement to strengthen the competitive

edge; the yield has reached 85%.

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